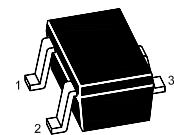


MMBT8550W

PNP Silicon Epitaxial Planar Transistor

for switching and amplifier applications



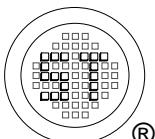
1.Base 2.Emitter 3.Collector
SOT-323 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Emitter Voltage	$-V_{CEO}$	25	V
Collector Base Voltage	$-V_{CBO}$	40	V
Emitter Base Voltage	$-V_{EBO}$	6	V
Collector Current	$-I_C$	600	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{Stg}	- 55 to + 150	°C

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE} = 1 \text{ V}$, $-I_C = 100 \text{ mA}$ at $-V_{CE} = 1 \text{ V}$, $-I_C = 500 \text{ mA}$	h_{FE} h_{FE} h_{FE}	100 160 40	- - -	250 400 -	- - -
Collector Cutoff Current at $-V_{CB} = 35 \text{ V}$	$-I_{CBO}$	-	-	100	nA
Collector Saturation Voltage at $-I_C = 500 \text{ mA}$, $-I_B = 50 \text{ mA}$	$-V_{CE(sat)}$	-	-	0.5	V
Base Saturation Voltage at $-I_C = 500 \text{ mA}$, $-I_B = 50 \text{ mA}$	$-V_{BE(sat)}$	-	-	1.2	V
Collector Emitter Breakdown Voltage at $-I_C = 2 \text{ mA}$	$-V_{(BR)CEO}$	25	-	-	V
Collector Base Breakdown Voltage at $-I_C = 10 \mu\text{A}$	$-V_{(BR)CBO}$	40	-	-	V
Emitter Base Breakdown Voltage at $-I_E = 100 \mu\text{A}$	$-V_{(BR)EBO}$	6	-	-	V
Gain Bandwidth Product at $-V_{CE} = 5 \text{ V}$, $-I_C = 10 \text{ mA}$, $f = 50 \text{ MHz}$	f_T	-	100	-	MHz
Collector Base Capacitance at $-V_{CB} = 10 \text{ V}$, $f = 1 \text{ MHz}$	C_{CBO}	-	12	-	pF



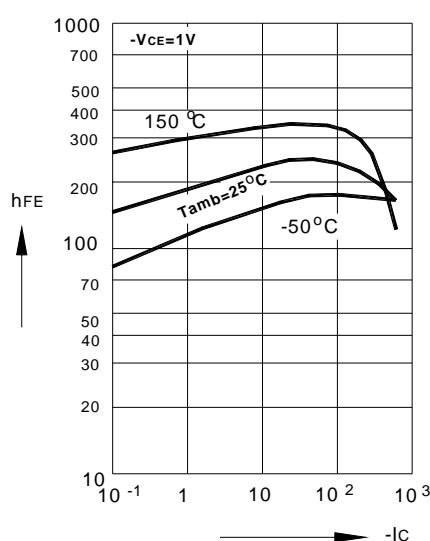
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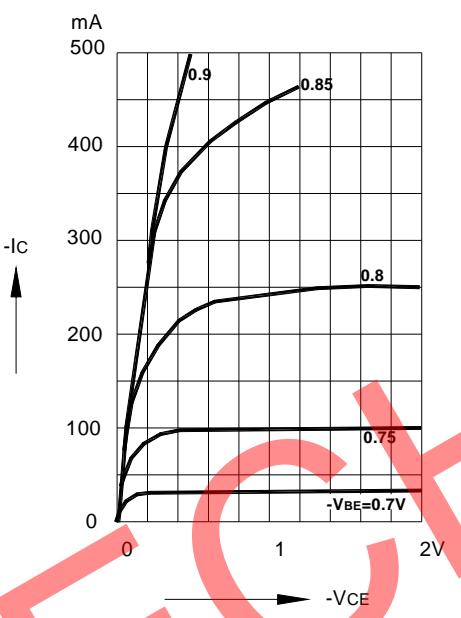
Dated : 11/08/2006

MMBT8550W

DC current gain
versus collector current



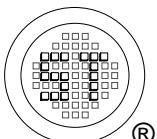
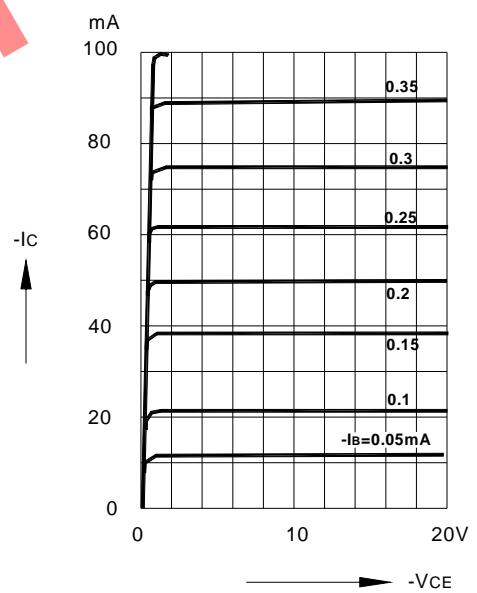
Common emitter
collector characteristics



Common emitter
collector characteristics



Common emitter
collector characteristics



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